Ordering number: EN 572D
查询2SA1016供应商

SANYO

No.572D

2SA1016,1016K/2SC2362,2362K

PNP/NPN Epitaxial Planar Silicon Transistors

High-Voltage Low-Noise Amp Applications

( ): 2SA1016,1016K

Absolute Maximum Ratings at T_a=25°C

		2SA1016,2SC2362	2SA1016K,2SC2362K	unit
Collector to Base Voltage	V_{CBO}	(-)120	(-)150	V
Collector to Emitter Voltage	V_{CEO}	(-)100	(-)120	V
Emitter to Base Voltage	V_{EBO}	(-)5		V
Collector Current	I_C	(-)50		mA
Collector Current(Pulse)	I_{CP}	(-)100		mA
Collector Dissipation	P_C	400		mW
Junction Temperature	Tj	125		°C
Storage Temperature	T_{stg}	-55 to +125		°C

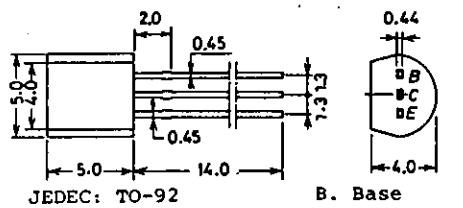
Electrical Characteristics at T_a=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=(-)80V, I_E=0			(-)1.0	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(-)4V, I_C=0			(-)1.0	μA
DC Current Gain	h_{FE}	V_{CE}=(-)6V, I_C=(-)1mA	160*		960*	
Gain-Bandwidth Product	f_T	V_{CE}=(-)6V, I_C=(-)1mA		(110) 130		MHz
Output Capacitance	C_{ob}	V_{CB}=(-)10V, f=1MHz		(2.2) 1.8		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=(-)10mA, I_B=(-)1mA			(-)0.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=(-)10μA, I_E=0 [A1016,C2362]	(-)120			V
		I_C=(-)10μA, I_E=0 [A1016K,C2362K]	(-)150			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=(-)1mA, R_{BE}=∞ [A1016,C2362]	(-)100			V
		I_C=(-)1mA, R_{BE}=∞ [A1016K,C2362K]	(-)120			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E=(-)10μA, I_C=0	(-)5			V
Noise Level	$V_{NO(ave)}$	V_{CC}=30V, I_C=1mA, Rg=56kΩ VG=77dB/1kHz			35	mV
Noise Peak Level	$V_{NO(peak)}$	" " "			200	mV

* The 2SA1016,K / 2SC2362,K are classified by 1mA h_{FE} as follows :

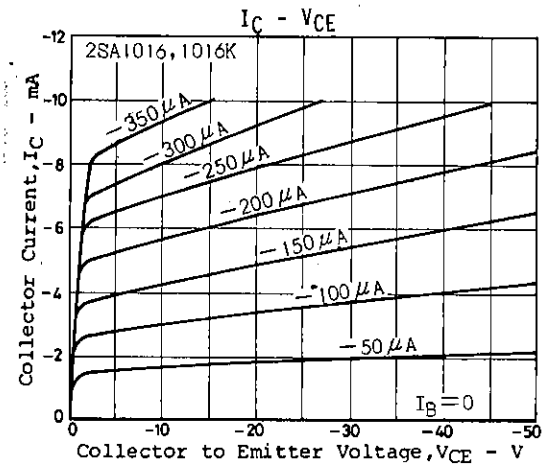
160 F 320	280 G 560	480 H 960

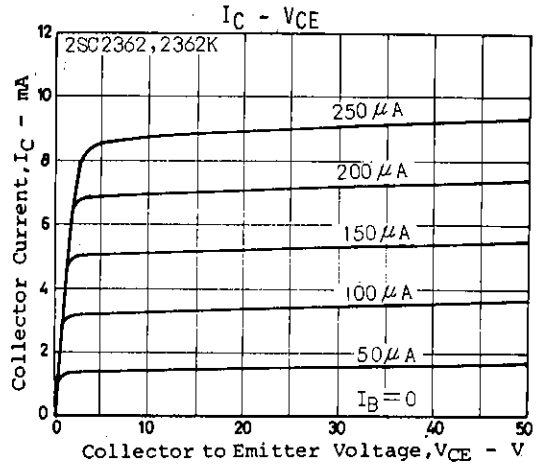
Package Dimensions
(unit: mm) 2003A

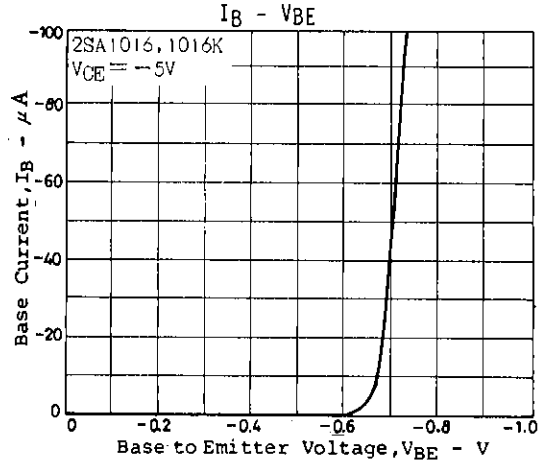


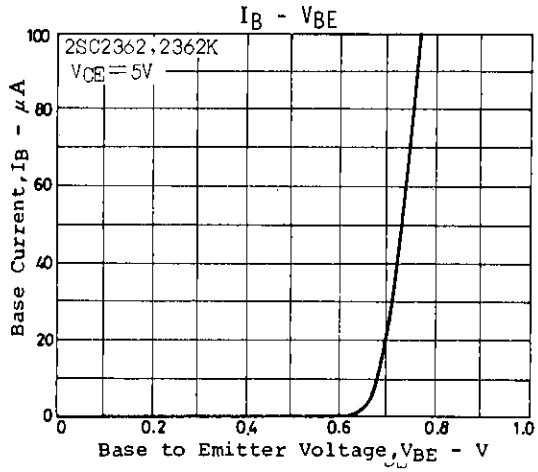
JEDEC: TO-92
EIAJ : SC-43
SANYO: NP

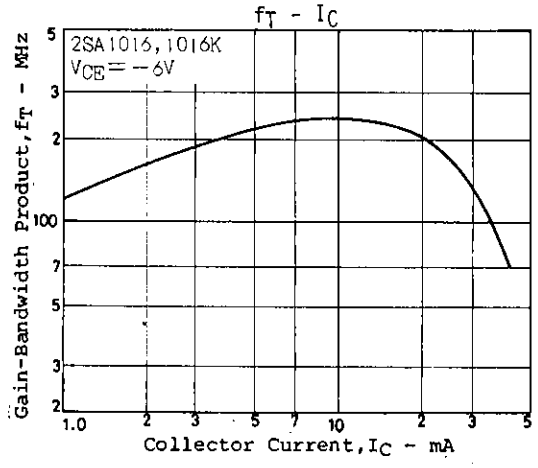
B. Base
C. Collector
E. Emitter

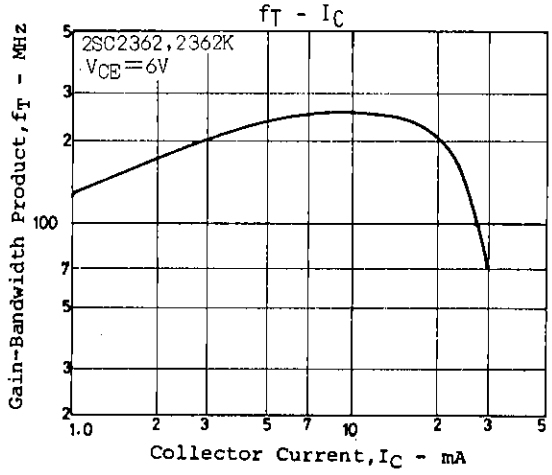

I_C - V_{CE}
2SA1016, 1016K
−350 μA
−300 μA
−250 μA
−200 μA
−150 μA
−100 μA
−50 μA
I_B=0
Collector Current, I_C - mA
Collector to Emitter Voltage, V_{CE} - V

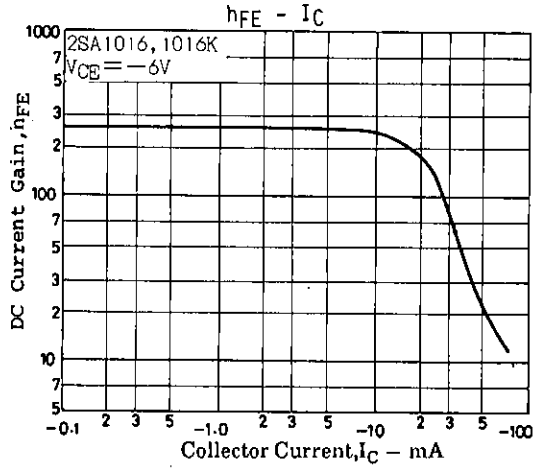

I_C - V_{CE}
2SC2362, 2362K
250 μA
200 μA
150 μA
100 μA
50 μA
I_B=0
Collector Current, I_C - mA
Collector to Emitter Voltage, V_{CE} - V

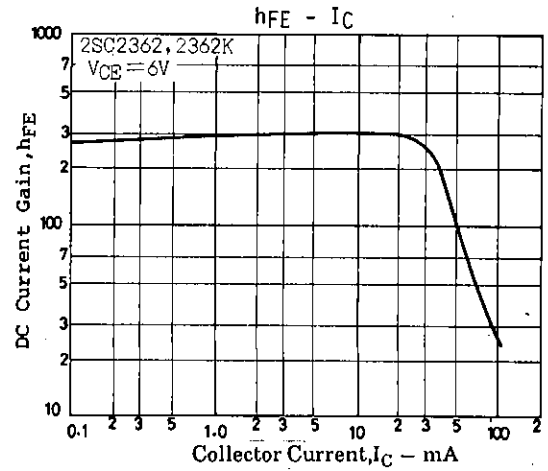

I_B - V_{BE}
2SA1016, 1016K
V_{CE} = −5V
Base Current, I_B - μA
Base to Emitter Voltage, V_{BE} - V

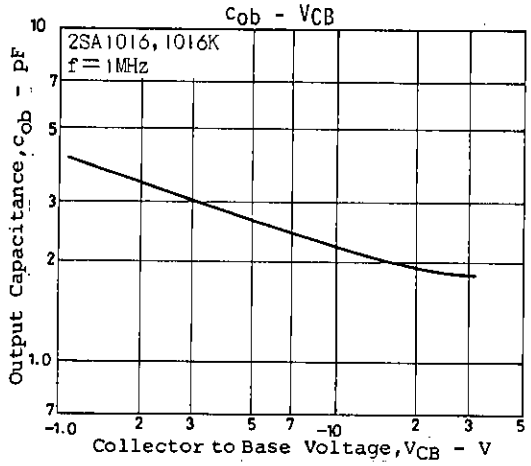

I_B - V_{BE}
2SC2362, 2362K
V_{CE} = 5V
Base Current, I_B - μA
Base to Emitter Voltage, V_{BE} - V

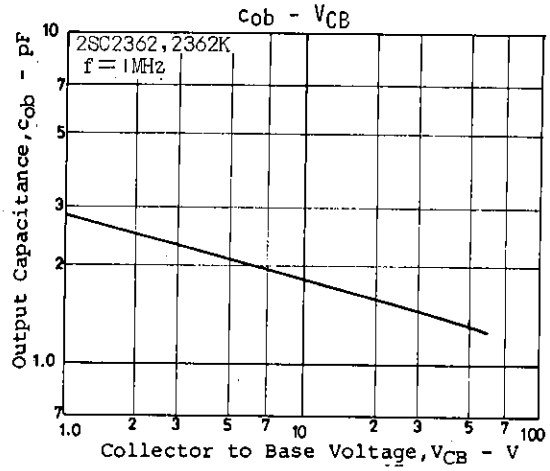

f_T - I_C
2SA1016, 1016K
V_{CE} = −6V
Gain-Bandwidth Product, f_T - MHz
Collector Current, I_C - mA

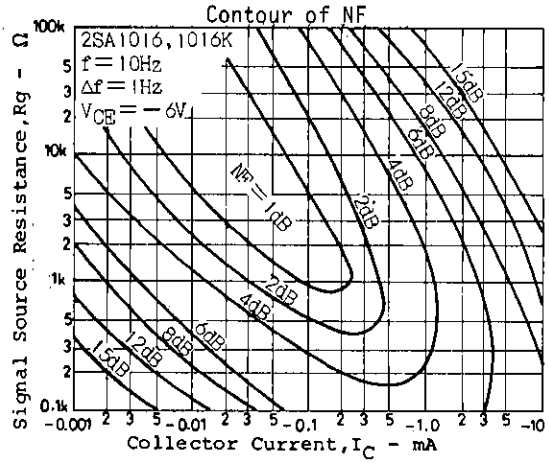

f_T - I_C
2SC2362, 2362K
V_{CE} = 6V
Gain-Bandwidth Product, f_T - MHz
Collector Current, I_C - mA

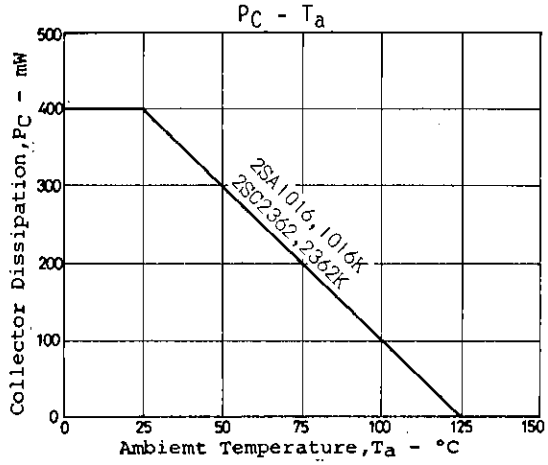

h_{FE} - I_C
2SA1016, 1016K
V_{CE} = −6V
DC Current Gain, h_{FE}
Collector Current, I_C − mA

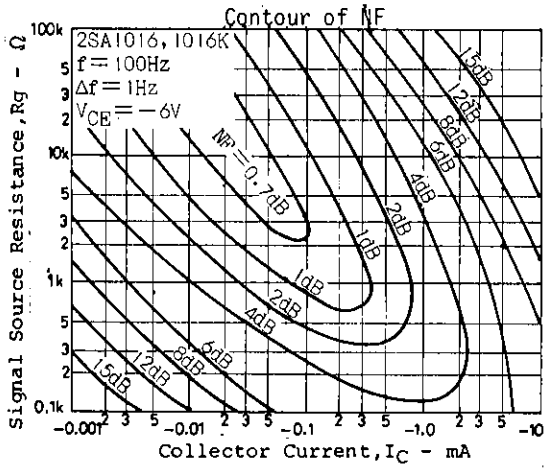

h_{FE} - I_C
2SC2362, 2362K
V_{CE} = 6V
DC Current Gain, h_{FE}
Collector Current, I_C − mA

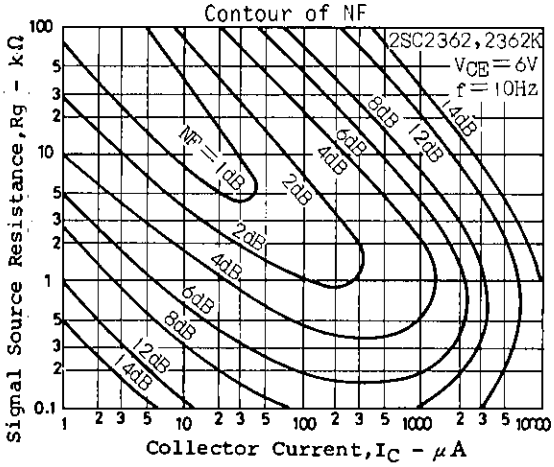

Cob - VCB
2SA1016,1016K
f=1MHz
Output Capacitance,Cob - pF
Collector to Base Voltage,VCB - V

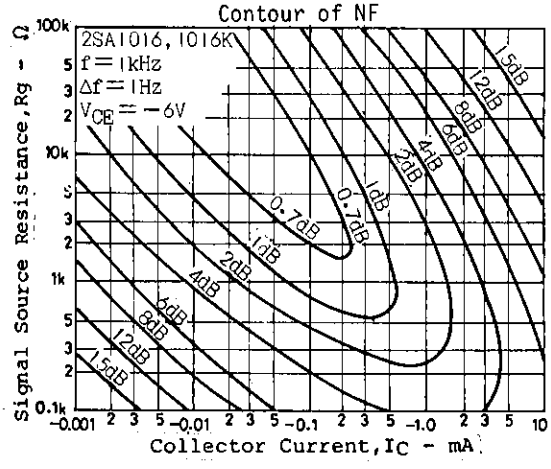

Cob - VCB
2SC2362,2362K
f=1MHz
Output Capacitance,Cob - pF
Collector to Base Voltage,VCB - V

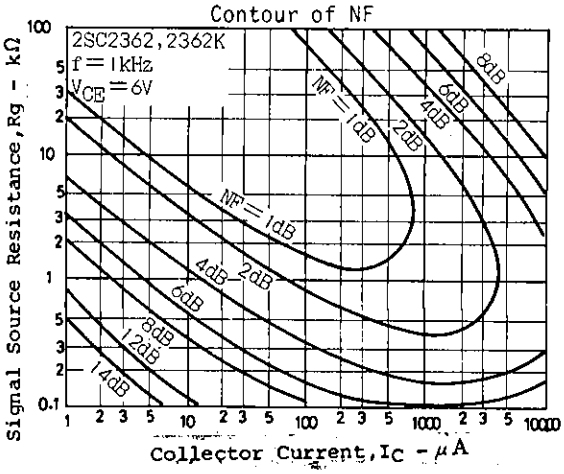

Contour of NF
2SA1016,1016K
f=10Hz
Δf=1Hz
VCE=−6V
NF=1dB
Signal Source Resistance,Rg - Ω
Collector Current,IC - mA

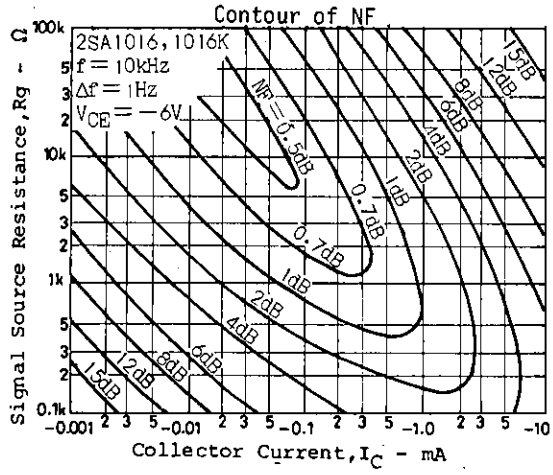

PC - Ta
2SA1016,1016K
2SC2362,2362K
Collector Dissipation,PC - mW
Ambiemt Temperature,Ta - °C


Contour of NF
2SA1016,1016K
f=100Hz
Δf=1Hz
VCE=−6V
NF=0.7dB
Signal Source Resistance,Rg - Ω
Collector Current,IC - mA


Contour of NF
2SC2362,2362K
VCE=6V
f=10Hz
NF=1dB
Signal Source Resistance,Rg - kΩ
Collector Current,IC - μA


Contour of NF
2SA1016,1016K
f=1kHz
Δf=1Hz
VCE=−6V
NF=0.7dB
Signal Source Resistance,Rg - Ω
Collector Current,IC - mA


Contour of NF
2SC2362,2362K
f=1kHz
VCE=6V
NF=1dB
Signal Source Resistance,Rg - kΩ
Collector Current,IC - μA



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